

LIST OF PUBLICATIONS

(Scientific Papers)

Masakazu Aono

431. Mechanism for conducting filament growth in self-assembled polymer thin films for redox-based atomic switches,
K. Krishnan, T. Tsuruoka, C.R. Mannequin, and M. Aono
Adv. Mater. 28 (2016) 640-648.
430. The way to nanoarchitectonics and the way of nanoarchitectonics,
M. Aono and K. Ariga ,
Adv. Mater. 28 (2016) 989-992.
429. On-surface synthesis of single conjugated polymer chains for single-molecule devices,
Y. Okawa, M. Swapan, M. Marina Vadimovna, E. Verveniots, and M. Aono,
On-surface Synthesis (2016) 167-179.
428. Controlled fabrication of silk protein sericin mediated hierarchical hybrid flowers and their excellent adsorption capability of heavy metal ions of Pb(II) Cd(II) and Hg(II),
P. Koley, M. Sakurai, and M. Aono,
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427. Direct observation of anodic dissolution and filament growth behavior in polyethylene-oxide-based atomic switch structures,
K. Krishnan, T. Tsuruoka, and M. Aono,
Jpn. J. Appl. Phys 55 (2016) 06GK02-1.
426. Humidity effects on the redox reactions and ionic transport in a Cu/Ta₂O₅/Pt atomic switch structure,
T. Tsuruoka, I. Valov, C.R. Mannequin, T. Hasegawa, R. Waser, and M. Aono,
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425. Decision maker based on atomic switches,
S. Kim, T. Tsuruoka, T. Hasegawa, M. Aono, K. Terabe, and M. Aono,
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424. In-situ tuning of magnetization and magnetoresistance in Fe₃O₄ thin film achieved with all-solid-state redox device,
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422. Composition of thin Ta₂O₅ films deposited by different methods and the effect of humidity on their resistive switching behavior,
C.R. Mannequin, T. Tsuruoka, T. Hasegawa, and M. Aono,
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421. Nanoionic devices enabling a multitude of new features,
K. Terabe, T. Tsuchiya, R. Yang, and M. Aono,

- Nanoscale 8 (2016) 13873-13879.
420. Identification and roles of nonstoichiometric oxygen in amorphous Ta₂O₅ thin films deposited by electron beam and sputtering processes,
C.R. Mannequin, T. Tsuruoka, T. Hasegawa, and M. Aono,
Appl. Surf. Sci. 385 (2016) 426-435.
419. Kinetic factors determining conducting filament formation in solid polymer electrolyte based planar Devices,
K. Krishnan, M. Aono, and T. Tsuruoka
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418. Redox reactions at CuAg/Ta₂O₅ interfaces and the effects of Ta₂O₅ film density on the forming process in atomic switch structures,
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417. Tunable morphology from 2D to 3D in the formation of hierarchical architectures from a self-assembling dipeptide: thermal-induced morphological transition to 1D nanostructures,
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416. Dynamic moderation of an electric field using a SiO₂ switching layer in TaOx-based ReRAM,
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413. Ultrahigh-Gain Single SnO₂ Microrod Photoconductor on Flexible Substrate with Fast Recovery Speed,
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411. Effect of ionic conductivity on response speed of SrTiO₃-based all-solid-state electric-double-layer transistor,
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